

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Thyristor \ Diode Module

=2x 800 V

27 A

 V_{T} 1.27 V

Phase leg

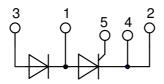
Part number

MCD26-08io1B



Backside: isolated

F1 E72873



Features / Advantages:

- Thyristor for line frequency
- Planar passivated chip
- Long-term stability
- Direct Copper Bonded Al2O3-ceramic

Applications:

- Line rectifying 50/60 Hz
- Softstart AC motor control
- DC Motor control
- Power converter AC power control
- Lighting and temperature control

Package: TO-240AA

- Isolation Voltage: 3600 V~
- Industry standard outline
- RoHS compliant
- Soldering pins for PCB mounting
- Base plate: DCB ceramic
- · Reduced weight
- Advanced power cycling

Terms _Conditions of usage:

The data contained in this product data sheet is exclusively intended for technically trained staff. The user will have to evaluate the suitability of the product for the intended application and the completeness of the product data with respect to his application. The specifications of our components may not be considered as an assurance of component characteristics. The information in the valid application- and assembly notes must be considered. Should you require product information in excess of the data given in this product data sheet or which concerns the specific application of your product, please contact your local sales office.

Due to technical requirements our product may contain dangerous substances. For information on the types in question please contact your local sales office.

Should you intend to use the product in aviation, in health or life endangering or life support applications, please notify. For any such application we urgently recommend

to perform joint risk and quality assessments;
the conclusion of quality agreements;

- to establish joint measures of an ongoing product survey, and that we may make delivery dependent on the realization of any such measures.

IXYS reserves the right to change limits, conditions and dimensions.

Data according to IEC 60747 and per semiconductor unless otherwise specified

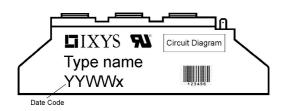
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Rectifier				 	Ratings	5	1
Symbol	Definition	Conditions		min.	typ.	max.	Un
V _{RSM/DSM}	max. non-repetitive reverse/forwa	rd blocking voltage	$T_{VJ} = 25^{\circ}C$			900	
V _{RRM/DRM}	max. repetitive reverse/forward bl	ocking voltage	$T_{VJ} = 25^{\circ}C$			800	į
I _{R/D}	reverse current, drain current	$V_{R/D} = 800 V$	$T_{VJ} = 25^{\circ}C$			100	μ
		$V_{R/D} = 800 V$	$T_{VJ} = 125^{\circ}C$			3	m
V _T	forward voltage drop	I _T = 40 A	$T_{VJ} = 25^{\circ}C$			1.27	
		$I_T = 80 \text{ A}$				1.64	
		$I_T = 40 \text{ A}$	T _{vJ} = 125°C			1.27	
		$I_{T} = 80 \text{ A}$				1.65	
I _{TAV}	average forward current	$T_C = 85^{\circ}C$	T _{vJ} = 125°C			27	
I _{T(RMS)}	RMS forward current	180° sine				42	
V _{T0}	threshold voltage		T _{v.i} = 125°C			0.85	
r _T	slope resistance } for power lo	ess calculation only	VJ			11	m!
R _{thJC}	thermal resistance junction to cas	e e				0.88	K/V
R _{thCH}	thermal resistance case to heatsin				0.20	*****	K/V
P _{tot}	total power dissipation		T _C = 25°C		0.20	115	V
l _{TSM}	max. forward surge current	t = 10 ms; (50 Hz), sine	$T_{VI} = 45^{\circ}C$			520	
TSM	max. Torward barge barrers	t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			560	
		t = 0.5 ms; (50 Hz), sine t = 10 ms; (50 Hz), sine	$T_{VJ} = 125$ °C			440	
		, , , , , , , , , , , , , , , , , , , ,	**			_	į
121	value for fueing	t = 8,3 ms; (60 Hz), sine	V _R = 0 V			475	I. A.S
l²t	value for fusing	t = 10 ms; (50 Hz), sine	$T_{VJ} = 45^{\circ}C$			1.35	kA ²
		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			1.31	1
		t = 10 ms; (50 Hz), sine	$T_{VJ} = 125$ °C			970	A ²
_		t = 8,3 ms; (60 Hz), sine	$V_R = 0 V$			940	A ²
C,	junction capacitance	$V_R = 400 V$ f = 1 MHz	$T_{VJ} = 25^{\circ}C$		22		р
P_{GM}	max. gate power dissipation	$t_P = 30 \mu s$	$T_{C} = 125^{\circ}C$			10	į
		t _P = 300 μs				5	٧
P _{GAV}	average gate power dissipation					0.5	۷
(di/dt) _{cr}	critical rate of rise of current	$T_{VJ} = 125 ^{\circ}\text{C}; f = 50 \text{Hz}$ re	petitive, $I_T = 45 A$			150	A/μ
		$t_P = 200 \mu s; di_G/dt = 0.45 A/\mu s;$					
		$I_G = 0.45 A; V = \frac{2}{3} V_{DRM}$ no	on-repet., $I_T = 27 A$			500	A/μ
(dv/dt) _{cr}	critical rate of rise of voltage	$V = \frac{2}{3} V_{DRM}$	$T_{VJ} = 125$ °C			1000	V/µ
		R _{GK} = ∞; method 1 (linear voltag	ge rise)				
V _{GT}	gate trigger voltage	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			1.5	,
			$T_{VJ} = -40$ °C			1.6	١
I _{GT}	gate trigger current	$V_D = 6 V$	$T_{VJ} = 25^{\circ}C$			100	m
		-	$T_{VJ} = -40$ °C			200	m
V _{GD}	gate non-trigger voltage	$V_D = \frac{2}{3} V_{DBM}$	T _{VJ} = 125°C			0.2	,
I _{GD}	gate non-trigger current	D DITIVI	70			10	m
-gb _L	latching current	t _p = 10 μs	T _{vJ} = 25°C			450	m
•L	atomig carrent	$I_{\rm G} = 0.45 \text{A}; \text{di}_{\rm G}/\text{dt} = 0.45 \text{A}/\mu \text{s}$				100	
	holding current	$V_D = 6 \text{ V } R_{GK} = \infty$	T _{vJ} = 25°C			200	m
l _н			$T_{VJ} = 25 \text{ C}$ $T_{VJ} = 25 \text{ °C}$				<u> </u>
t _{gd}	gate controlled delay time	$V_D = \frac{1}{2} V_{DRM}$				2	μ
	turn off time-	$I_G = 0.45 \text{ A}; \text{ di}_G/\text{dt} = 0.45 \text{ A}/\mu\text{s}$			150		-
tq	turn-off time	$V_R = 100 \text{ V}; I_T = 20 \text{ A}; V = \frac{2}{3}$			150		μ
		$di/dt = 10 A/\mu s dv/dt = 20 V/$	/μs t _p = 200 μs				1



Package	TO-240AA				ı	Ratings	S	
Symbol	Definition	Conditions			min.	typ.	max.	Unit
RMS	RMS current	per terminal					200	Α
T _{VJ}	virtual junction temperature				-40		125	°C
Top	operation temperature				-40		100	°C
T _{stg}	storage temperature				-40		125	°C
Weight						81		g
M _D	mounting torque				2.5		4	Nm
$\mathbf{M}_{_{T}}$	terminal torque				2.5		4	Nm
d _{Spp/App}	creepage distance on surface	striking distance through air	terminal to terminal	13.0	9.7			mm
d _{Spb/Apb}	creepage distance on surface	Striking distance through an	terminal to backside	16.0	16.0			mm
V _{ISOL}	isolation voltage	t = 1 second	50/60 Hz. RMS: IISOL ≤ 1 mA		3600			٧
.002		t = 1 minute			3000			٧



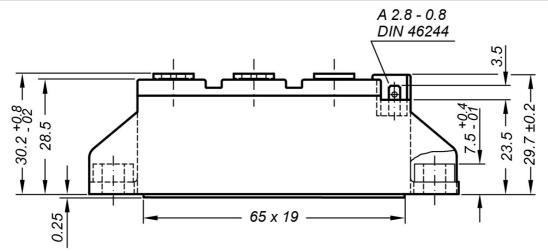
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	MCD26-08io1B	MCD26-08io1B	Box	36	500934

Similar Part	Package	Voltage class
MCMA35PD1200TB	TO-240AA-1B	1200
MCMA50PD1200TB	TO-240AA-1B	1200

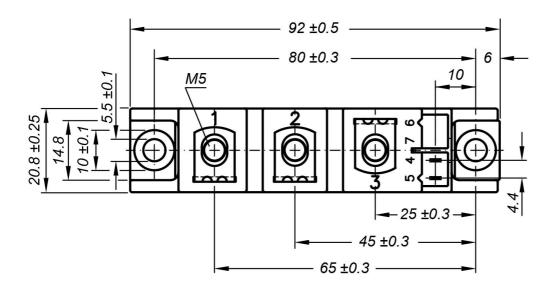
Equiva	alent Circuits for	Simulation	* on die level	T _{VJ} = 125 °C
$I \rightarrow V_0$)— <u>R</u> o	Thyristor		
V _{0 max}	threshold voltage	0.85		V
$R_{0 max}$	slope resistance *	9.8		$m\Omega$



Outlines TO-240AA

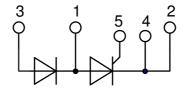


General tolerance: DIN ISO 2768 class "c"



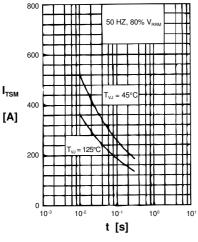
Optional accessories: Keyed gate/cathode twin plugs Wire length: 350 mm, gate = white, cathode = red UL 758, style 3751

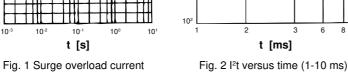
Type **ZY 200L** (L = Left for pin pair 4/5)





Thyristor





 I_{TSM} : Crest value, t: duration

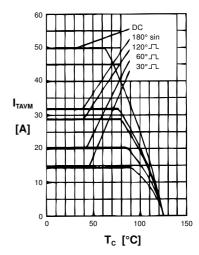
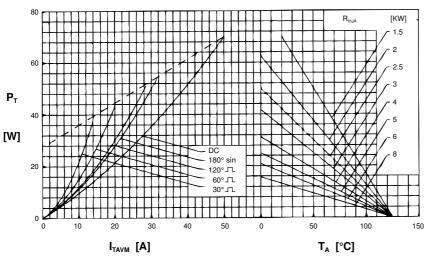


Fig. 3 Max. forward current at case temperature



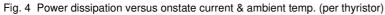
 $V_R = 0 V$

T_{v.i} = 125°C

t [ms]

l²t

[A2s]



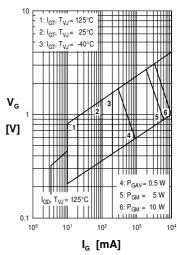


Fig. 5 Gate trigger charact.

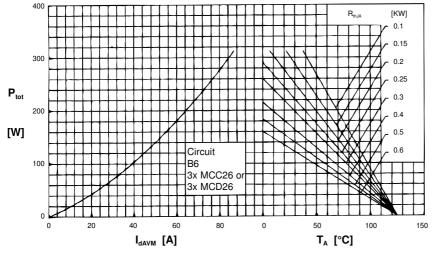


Fig. 6 Three phase rectifier bridge: Power dissipation versus direct output current and ambient temperature

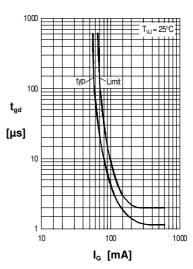


Fig. 7 Gate trigger delay time



Rectifier

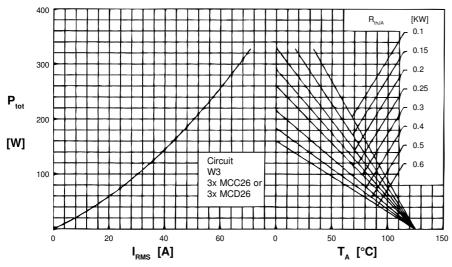


Fig. 8 Three phase AC-controller: Power dissipation vs. RMS output current and ambient temperature

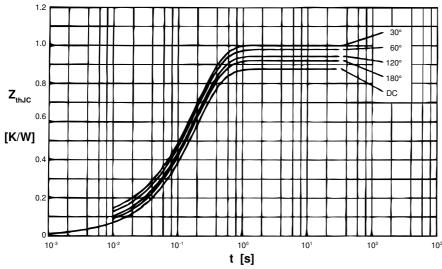


Fig. 9 Transient thermal impedance junction to case (per thyristor)

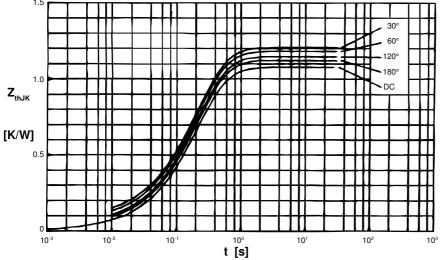


Fig. 10 Transient thermal impedance junction to heatsink (per thyristor)

R_{th.IC} for various conduction angles d:

nJC	-	
	d	R_{thJC} [K/W]
	DC	0.88
-	180°	0.92
-	120°	0.95
	60°	0.98
	30°	1 01

Constants for Z_{thJC} calculation:

i I	R _{thi} [K/W]	t _i [s]
1	0.019	0.0031
2	0.029	0.0216
3	0.832	0.1910

 R_{thJK} for various conduction angles d:

101		
	d	R _{thJK} [K/\
	DC	1.08
	180°	1.12
	120°	1.15
	60°	1.18
	30°	1.21

Constants for Z_{thJK} calculation:

i	R _{thi} [K/W]	t, [s]
1	0.019	0.0031
2	0.029	0.0216
3	0.832	0.1910
4	0.200	0.4500